Semicon West 2012: NCCAVS Junction Technology Seminar

Thursday July 12, 2012 Moscone South Esplanade, Room 305, **2012 Update on Junction Technology For Solar & Semiconductor**

10AM: Welcome & Acknowledgement of Sponsors by John Borland & Michael Current

Solar Technologies

10:05AM: Henry Hieslmair of Intevac,

"Engineering Advanced Solar Cells with High Throughput Ion Implantation".

10:30AM: Bert Allen of FISilicon,

"PVD-Si coatings for Process Chamber Shields & Low Cost 450 mm Test Wafers"

10:55AM: John Borland of J.O.B. Technologies,

"Selective and Homo Emitter Junction Formation Using Precise Dopant Concentration Control by Ion Implantation and Microwave, Laser or Furnace Annealing Techniques".

11:20PM: Karim Huet of Excico,

"Ultra Low Thermal Budget Laser Thermal Annealing for 3D Semiconductor and Photovoltaic Applications".

11:45-12:30PM Lunch Served & Break

Semiconductor Technologies

12:30PM: Karuppanan Sekar of Nissin ion,

"Applications of Cluster Carbon-a Review".

12:55PM: Michiro Sugitani of SEN,

"Simulation Study of Conformal Doping by I/I and MTI".

1:20PM: Michael Current of IBS,

"Emerging Applications for Plasma Immersion Implantation".

1:45PM: Paul Timans of Mattson Technology,

"Flat-Top Flash Annealing for Advanced CMOS Processing".

2:10PM: Jeff Hebb of Ultratech,

"Laser Spike Anneal for sub-28nm Non-USJ Applications".

2:35PM: Afternoon Ice Cream Break

2:55PM: Walt Johnson of KT,

"Ion Implant Dose Monitoring for 450mm Wafers".

3:20PM: Peter Nielsen of CAPRES,

"Microprobe Metrology for direct Sheet Resistance and Mobility Characterization".

3:45PM: Closing remarks